

A Comparative Study of Si₃N₄ and Al₂O₃ as Dielectric Materials for Pre-Charged Collapse-Mode CMUTs

Saccher, Marta; Schaijk, Rob van; Kawasaki, Shinnosuke; Klootwijk, Johan H.; Rashidi, Amin; Giagka, Vasiliki; Savoia, Alessandro Stuart; Dekker, Ronald

DOI

[10.1109/IUS51837.2023.10307389](https://doi.org/10.1109/IUS51837.2023.10307389)

Publication date

2023

Document Version

Final published version

Published in

Proceedings of the 2023 IEEE International Ultrasonics Symposium (IUS)

Citation (APA)

Saccher, M., Schaijk, R. V., Kawasaki, S., Klootwijk, J. H., Rashidi, A., Giagka, V., Savoia, A. S., & Dekker, R. (2023). A Comparative Study of Si₃N₄ and Al₂O₃ as Dielectric Materials for Pre-Charged Collapse-Mode CMUTs. In *Proceedings of the 2023 IEEE International Ultrasonics Symposium (IUS)* IEEE. <https://doi.org/10.1109/IUS51837.2023.10307389>

Important note

To cite this publication, please use the final published version (if applicable). Please check the document version above.

Copyright

Other than for strictly personal use, it is not permitted to download, forward or distribute the text or part of it, without the consent of the author(s) and/or copyright holder(s), unless the work is under an open content license such as Creative Commons.

Takedown policy

Please contact us and provide details if you believe this document breaches copyrights. We will remove access to the work immediately and investigate your claim.

Green Open Access added to TU Delft Institutional Repository

'You share, we take care!' - Taverne project

<https://www.openaccess.nl/en/you-share-we-take-care>

Otherwise as indicated in the copyright section: the publisher is the copyright holder of this work and the author uses the Dutch legislation to make this work public.

A Comparative Study of Si_3N_4 and Al_2O_3 as Dielectric Materials for Pre-Charged Collapse-Mode CMUTs

Marta Saccher^{*}, Rob van Schaijk[§], Shinnosuke Kawasaki[‡], Johan H. Klootwijk[§], Amin Rashidi^{*}, Vasiliki Giagka^{*†}, Alessandro Stuart Savoia[¶] and Ronald Dekker^{*§}

^{*}Department of Microelectronics, Delft University of Technology, Delft, the Netherlands

[†]Department of System Integration and Interconnection Technologies, Fraunhofer IZM, Berlin, Germany

[‡]TNO/Holst Centre, Eindhoven, the Netherlands

[§]MEMS & Micro Devices, Philips, Eindhoven, the Netherlands

[¶]Department of Industrial, Electronic, and Mechanical Engineering, Roma Tre University, Rome, Italy

Abstract—Capacitive Micromachined Ultrasound Transducers (CMUTs) have many advantages compared to other ultrasonic transducer technologies, especially for implantable devices. However, they require a high bias voltage for efficient operation. To eliminate the need for an external bias voltage, a charge storage layer can be embedded in the dielectric. This study aims to compare the performance of Si_3N_4 and Al_2O_3 when used as a charge storage layer. By measuring the shift in the C-V curve, Si_3N_4 exhibits a larger shift than Al_2O_3 , indicating a better charge-trapping capability. When using the pre-charged CMUTs as power receivers, the Si_3N_4 version harvested up to 80 mW - only a few mW more than the Al_2O_3 - with an efficiency of about 50%. Accelerated Lifetime Tests predict a lifetime of about 7.8 and 1.2 years for Si_3N_4 and Al_2O_3 respectively.

Index Terms—pre-charged CMUT, Capacitive Micromachined Ultrasound Transducers, zero-bias transducers, ultrasonic power transfer

I. INTRODUCTION

Capacitive Micromachined Ultrasound Transducers (CMUTs) have gained increasing attention as power receivers for biomedical implants due to their manufacturing scalability and biocompatibility. CMUTs can be operated in two modes: non-collapse-mode, and collapse-mode. The collapse-mode occurs when the top membrane makes partial contact with the dielectric layer above the bottom electrode, achieved by applying a high DC voltage that causes the top membrane to snap down. The bias voltage typically ranges from 30 V to 70 V, resulting in enhanced transmit and receive sensitivity, and an output pressure up to three times greater compared to conventional mode [1], [2]. This increase is due to the higher electric field in the vacuum cavity caused by the high bias voltage and smaller effective gap height. However, such high DC biases are better avoided in the body.

To address the issue of external bias voltage, a charge storage layer, such as Al_2O_3 , can be incorporated into the dielectric stack. By trapping a sufficient amount of charge in this layer, a built-in bias is created, ensuring that the CMUT

This work was funded by the ECSEL Joint Undertaking project Moore4Medical, grant number H2020-ECSEL-2019IA-876190.

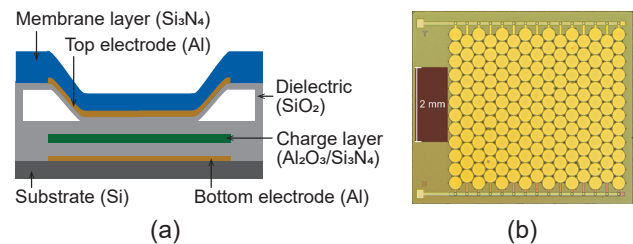


Fig. 1. (a) Schematic of collapse-mode CMUT with charge trapping layer in the dielectric. (b) Microscope view of the fabricated CMUT array.

remains in permanent collapse-mode [3], [4]. Besides Al_2O_3 , other materials capable of retaining enough charge can also be employed. Previous studies have utilized pre-charged CMUTs with Si_3N_4 or SiO_2 in the dielectric [2], [5]–[7]. Park et al. [7] and Choi et al. [5] have demonstrated the feasibility of pre-charged CMUTs with Si_3N_4 as the dielectric, exhibiting good charge retention over time, even at high temperatures. However, the reported pre-charged CMUTs are mostly focused on non-collapse-mode operation, with the exception of Ho et al. [6]. It is evident from these studies that trapping sufficient charge to achieve a pre-charged collapse-mode CMUT is challenging, and the choice of material for the charge-trapping layer is crucial. Choi et al. [5] compared the performance of Si_3N_4 - SiO_2 and SiO_2 as charging layers, concluding that Si_3N_4 maintains its performance for a longer duration due to superior charge retention. The objective of this study is to compare the performance of Si_3N_4 and Al_2O_3 as charge storage layers in the dielectric of collapse-mode CMUTs. Additionally, the performance of CMUTs as power receivers is evaluated.

II. DEVICE PREPARATION AND CHARACTERIZATION

A. CMUT fabrication

The CMUTs utilized in this study are circular cells with a diameter of 355 μm , fabricated using a standard sacrificial release processing technique. The dielectric layer consists of a

stack of SiO_2 \ charge layer \ SiO_2 , a vacuum gap, and an additional layer of SiO_2 . Two versions of CMUTs were fabricated and analyzed: the first version has an ALD-deposited Al_2O_3 charge layer, while the second has a PECVD-deposited Si_3N_4 charge layer. Both variants have a charge layer thickness of 200 nm, and the Equivalent Oxide Thickness (EOT) measures 320 nm and 350 nm for the Al_2O_3 and Si_3N_4 variant, respectively. A $5 \times 5 \text{ mm}^2$ single-element transducer, consisting of 173 CMUT cells electrically connected in parallel, was fabricated. Figure 1 depicts the schematic cross-section of the CMUT, and a microscope photograph of the fabricated device.

B. CMUT pre-charging and characterization

In a previous study, we established that by applying an electric field above 7 – 8 MV/cm for a few minutes, a stable pre-charged CMUT is produced [4]. In this study, we investigated the impact of charging the devices with varying electric fields. We selected charging voltages corresponding to electric fields ranging from 7.5 to 8.5 MV/cm, both with positive and negative polarity with respect to the bottom electrode. Each charging voltage was applied to a pristine device for 5 minutes. Subsequently, we measured the Capacitance-Voltage (C-V) curves to assess the shift in collapse voltage resulting from the charge stored in the dielectric. To minimize any alteration of the stored charge in the device, we employed a fast C-V protocol, with a voltage sweep rate of 80 V/ms. For the C-V measurement, a small AC signal at 125 MHz was superimposed on a 200 Hz triangular wave varying between 0 V and ± 120 V. The change in the phase of the impedance when the CMUT goes in and out of collapse is used to draw the C-V curve. Two measurement protocols were used: a DC bipolar sweep between positive and negative voltages for uncharged devices, and a DC unipolar sweep for either only positive or negative voltages, for devices charged with positive and negative polarity, respectively.

III. RESULTS AND DISCUSSION

A. Comparison of charge trapping

In Fig. 2(a), we compare the C-V curves of the two CMUT variants when charged with an electric field of 8 MV/cm with positive or negative polarity, to that of corresponding pristine devices. The C-V curve of both pristine devices exhibits symmetry around 0 V, indicating that the CMUT is not in a collapsed state and has no charge stored in the dielectric. Conversely, the pre-charged devices show a shift in the point of minimum capacitance of 60 to 80 V, indicating that they are in a collapsed state even at 0 V bias, and the presence of charge stored in the dielectric. Furthermore, we observe that the Si_3N_4 variant exhibits a larger shift in the C-V curve compared to Al_2O_3 for both polarities (Fig. 2(a)). This could be due to the different deposition method (ALD vs PECVD) and not (only) the different dielectric material of the two devices, and will be investigated in the future. Additionally, charging the device with a negative polarity results in a slightly larger shift in the C-V curve compared to positive polarity.

Figures 2(b) and (c) depict the impact of different charging electric fields on the shift in the C-V curves for the Si_3N_4 and Al_2O_3 variants, respectively. As expected, the shift becomes more significant for higher charging electric fields due to increased current tunneling through the CMUT dielectric. Moreover, charging Al_2O_3 devices with an electric field exceeding 8 MV/cm was only feasible with negative polarity, as devices charged with positive polarity experienced dielectric breakdown. In contrast, the Si_3N_4 variant tolerated charging electric fields up to 8.5 MV/cm without encountering any breakdown, regardless of polarity. Although the observed difference in breakdown points between positive and negative polarity was not evident for Si_3N_4 , it is possible that the difference exists but is smaller compared to Al_2O_3 . This can be attributed to the differing charging mechanisms and characteristics of the two dielectric materials.

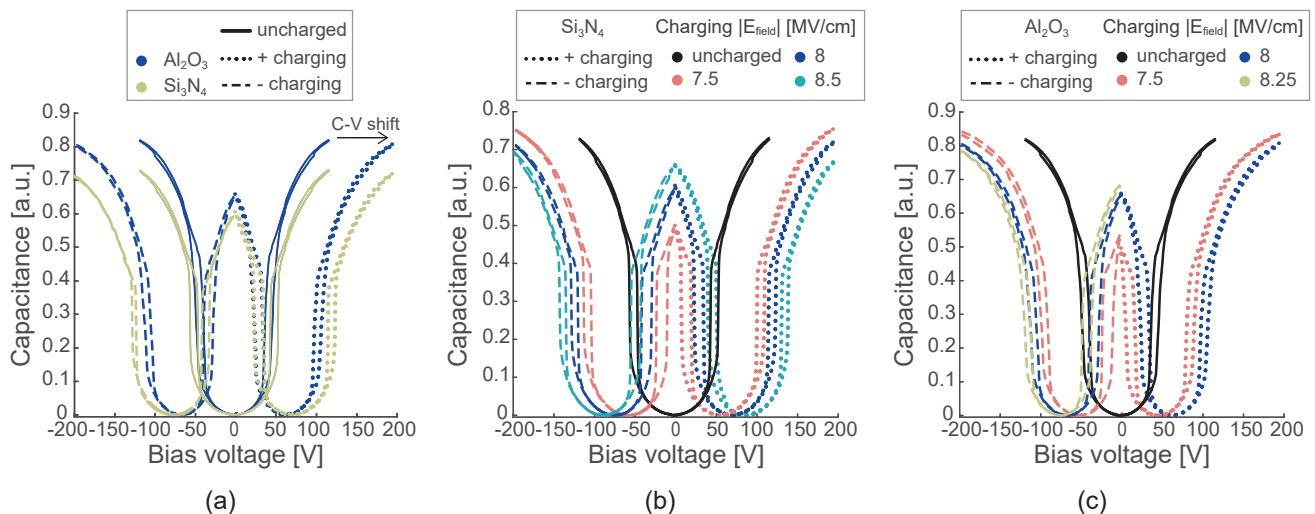


Fig. 2. (a) Comparison of C-V curve shift between Si_3N_4 and Al_2O_3 samples when charged with ± 8 MV/cm electric field. (b) Comparison of C-V curve shift for Si_3N_4 samples when charged with different electric fields and polarity. (c) Same as (b) but for Al_2O_3 .

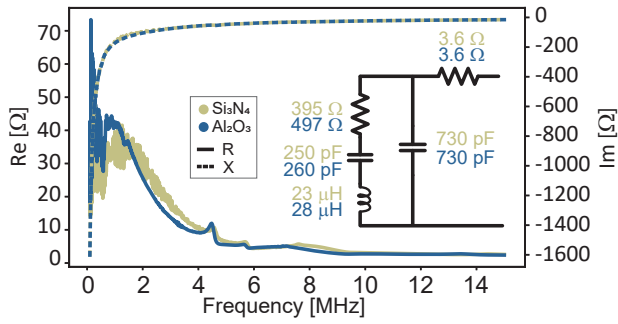


Fig. 3. Electrical impedance of the pre-charged collapse-mode CMUTs measured in water and corresponding BVD model values for the two device variants.

B. Pre-charged CMUT electro-mechanical characteristics

To evaluate the pre-charged collapse-mode CMUTs as wireless power receivers, we chose to compare devices charged with an electric field of -8 MV/cm as this was the highest electric field with which both variants could be charged. The CMUTs were wire-bonded to a PCB and coated with a thin layer of PBR (polybutadiene rubber). After charging the CMUTs, the shift in the C-V curve was 77 V and 68 V for the Si_3N_4 and Al_2O_3 variants, respectively, which can be considered as a built-in DC bias.

After charging, we measured their impedance in water with an impedance analyzer (Keithley E4990A, Keysight Technologies), and extracted the values of the Butterworth-Van Dyke (BVD) model components (Fig. 3). Both devices have a center frequency of around 2 MHz in water, and a typical bandwidth between 105% and 120% . Additionally, the BVD model incorporates a 3.6Ω parasitic resistance connected in series with the CMUT model. This resistance arises from the electrical interconnects between the CMUT array and the wire-bonding pads.

C. Maximum power transfer

To evaluate the pre-charged collapse-mode CMUTs as ultrasound power receivers, we conducted a power transfer experiment. A lower power carrier frequency is favorable in ultrasonic power delivery since it results in lower propagation losses for ultrasonic waves traveling through the tissue. Therefore, for this study, we chose a carrier frequency of 1 MHz . We used a circular single-element PZT piston transducer with a center frequency of 1 MHz and a diameter of 39 mm as the transmitting (TX) transducer. The receiving (RX) transducers were the two pre-charged CMUT variants. Both the TX and RX transducers were immersed in a water tank and aligned at the center, with a distance of 22 cm between them, which corresponds to the TX's natural focus distance. The pressure field generated by the TX transducer at this distance was previously measured by scanning a plane using a needle hydrophone parallel to the surface of the TX (Fig. 4(a)).

To maximize the power transfer efficiency, a matching network was connected to the CMUTs. In this study, we opted for a parallel matching approach, where the value of

the optimal load is the conjugate of the measured impedance at the chosen frequency. At 1 MHz , the BVD model of the two CMUTs devices can be simplified with a resistor in parallel with a capacitor. According to the maximum power transfer theorem, the optimal load connected in parallel to the CMUTs, consists of an inductor (L_{load}) and a resistor (R_{load}). The optimal inductor compensates for the equivalent capacitance of the BVD model, while the resistor should have the same value as the equivalent resistor of the BVD model. We determined the value of the matching inductor by testing components with values close to the conjugate of the equivalent electrical capacitance of the CMUT variants. A potentiometer was then used to find the optimal resistance value for maximizing the received power (Fig. 4(b)).

We applied a sine burst signal with an amplitude of 70 V and 10 cycles at a pulse repetition frequency of 1 kHz to the TX transducer, resulting in an instant acoustic intensity of 720 mW/cm^2 averaged across the CMUT surface. This intensity adheres to the FDA safety limit for the use of ultrasound in the body. The power at R_{load} was calculated using $P = V_{\text{pp}}^2 / (8 \cdot R_{\text{load}})$, where V_{pp} is the peak-to-peak voltage at the load. The maximum harvested power was 80 mW with the Si_3N_4 CMUT and 77 mW with the Al_2O_3 variant. The inset in Fig. 4(b) shows the corresponding acoustic-to-electrical power conversion efficiency of the CMUTs, calculated as the ratio between the acoustic power at the CMUT surface (instant acoustic intensity \times CMUT area) and the maximum harvested power, which reaches approximately 50% . The marginal difference in the maximum harvested power between the two devices can be attributed to an imperfect load matching for the Al_2O_3 version, primarily due to the limitations in available inductor values. However, it is important to note that this discrepancy is not significant enough to give preference to one material over the other.

Considering the integration of the CMUT devices into an ASIC, the requirement for a matching inductor poses a significant challenge, especially when inductors of tens of μH are needed, as in this case. To address this issue, we evaluated the power conversion efficiency with a purely resistive load by repeating the previous experiment. In this case, the load value needs to be matched to the modulus of the impedance of the simplified BVD model. Under these conditions, the maximum harvested power was 35 mW with the Si_3N_4 variant and 30 mW with the Al_2O_3 variant (Fig. 4(c)). The corresponding power conversion efficiency was approximately 20% . Table I summarizes the data obtained from the power transfer experiment.

D. Lifetime

To estimate the lifetime of the devices, Accelerated Lifetime Tests (ALT) have been performed with temperature as an accelerating factor. We placed the pre-charged CMUTs on a hotplate set at temperatures ranging from 140°C to 160°C , and the impedance was measured at regular time intervals. The time to failure at different test temperatures, defined as when more than half of the CMUT membranes are out of collapse-

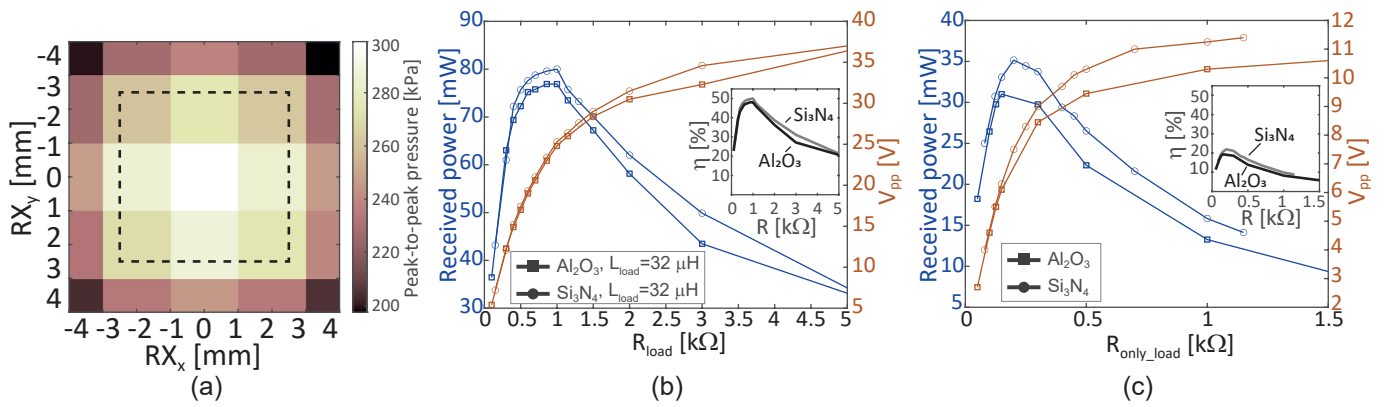


Fig. 4. (a) Pressure field at the location of the RX CMUT. The dashed line indicates the position of the CMUT. (b) and (c) Measurements with and without the matching inductor, respectively; power at R_{load} , and corresponding peak-to-peak voltage at load, for the two CMUT variants. Figure insets indicate the acoustic to electrical power conversion efficiency.

TABLE I
SUMMARY OF POWER TRANSFER EXPERIMENT

	$R_{eq}[\Omega]$	$C_{eq} [pF]$	$L_{load} [\mu H]$	$R_{load} [\Omega]$	$R_{only_load}[\Omega]$
Si_3N_4	900	920	32	1000	200
	Power			80	35
	η [%]			50	22
Al_2O_3	800	880	32	860	150
	Power			77	31
	η [%]			48	19

mode, was fitted using a previously defined method [4] to estimate the lifetime of the two CMUT variants at $37^\circ C$ (Fig. 5). The predicted lifetime of the Si_3N_4 variant is about 7.8 years, and 1.2 years for the Al_2O_3 variant. It should be noted that, although these ALT conditions may have accelerated the failure mechanisms, further tests are necessary to evaluate their lifetime under actual operational conditions. Nonetheless, these results demonstrate the potential of these devices.

IV. CONCLUSION

In this study, the performance of CMUTs with Si_3N_4 and Al_2O_3 charge storage layers was compared in terms of charge

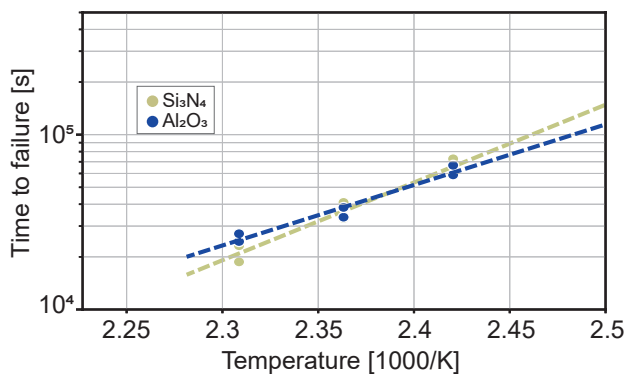


Fig. 5. Fitting of the ALT results to predict the CMUT lifetime.

trapping and power conversion efficiency. It was observed that, under the same charging electric field, a higher amount of charge could be stored in the Si_3N_4 variant compared to the Al_2O_3 variant. Furthermore, the Si_3N_4 variant demonstrated slightly higher power conversion efficiency than Al_2O_3 , with both variants achieving approximately 50% efficiency for a matched load and around 20% efficiency for a purely resistive load, indicating promising potentials for their integration into an ASIC to produce a single chip implantable medical device. Moreover, the estimated lifetime at body temperature yielded promising results for both variants. In conclusion, both materials showed good performance, and when selecting the dielectric material for pre-charged collapse-mode CMUTs, a trade-off between other factors such as ease of deposition, charging time, and charge retention should be carefully considered.

ACKNOWLEDGMENT

The authors would like to thank Eugene Timmering for fabricating the CMUT devices, Paul Dijkstra and Jacco Scheer for their assembly, Bart Mos for the acoustic measurements.

REFERENCES

- [1] K. K. Park, O. Oralkan, and B. T. Khuri-Yakub, "A comparison between conventional and collapse-mode capacitive micromachined ultrasonic transducers in 10-MHz 1-D arrays," *IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control*, vol. 60, no. 6, pp. 1245–1255, 2013.
- [2] A. Kshirsagar, A. Sampaleanu, R. Chee, W. Moussa, and R. J. Zemp, "Pre-charged CMUTs with efficient low-bias voltage operation for medical applications," in *2013 IEEE International Ultrasonics Symposium*.
- [3] M. Saccher, S. Kawasaki, and R. Dekker, "The long-term reliability of pre-charged CMUTs for the powering of deep implanted devices," in *2021 IEEE International Ultrasonics Symposium*, pp. 1–4.
- [4] M. Saccher, S. Kawasaki, J. H. Klootwijk, R. Van Schaijk, and R. Dekker, "Modeling and Characterization of Pre-Charged Collapse-Mode CMUTs," *IEEE Open Journal of Ultrasonics, Ferroelectrics, and Frequency Control*, vol. 3, pp. 14–28, 2023.
- [5] W. Y. Choi, C. H. Lee, Y. H. Kim, and K. K. Park, "Comparison of Si_3N_4 - SiO_2 and SiO_2 Insulation Layer for Zero-Bias CMUT Operation Using Dielectric Charging Effects," *IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control*, vol. 67, no. 4, pp. 879–882, 2020.
- [6] M.-C. Ho, M. Kupnik, K. K. Park, and B. T. Khuri-Yakub, "Long-term measurement results of pre-charged CMUTs with zero external bias operation," in *2012 IEEE International Ultrasonics Symposium*, pp. 89–92.
- [7] K. K. Park, M. Kupnik, H. J. Lee, O. Oralkan, B. T. Khuri-Yakub, and Ieee, *Zero-Bias Resonant Sensor with an Oxide-Nitride Layer as Charge Trap*, ser. IEEE Sensors. IEEE, 2010, pp. 1024–1028.